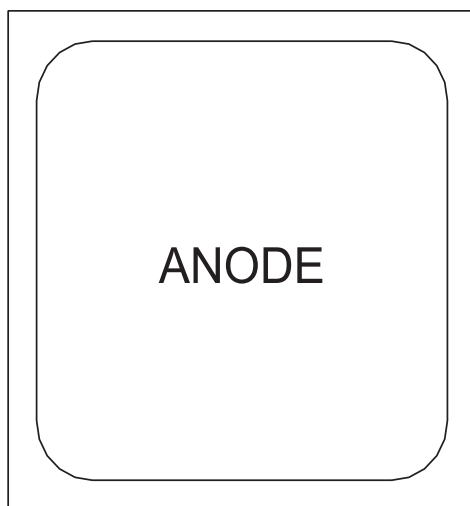


PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	25 x 25 MILS
Die Thickness	9.5 MILS
Anode Bonding Pad Area	14.5 x 14.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

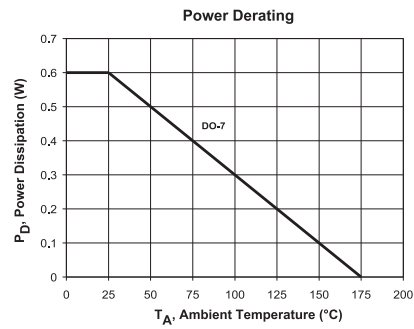
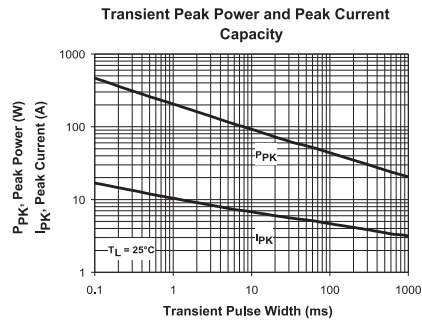
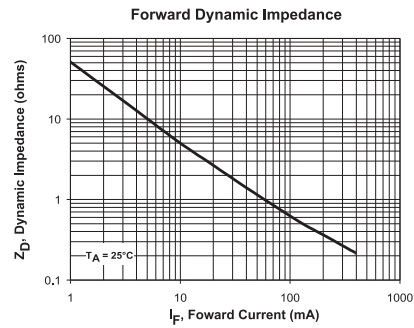
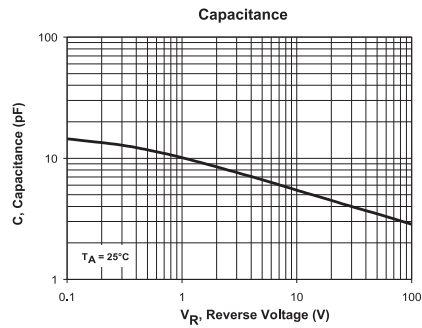
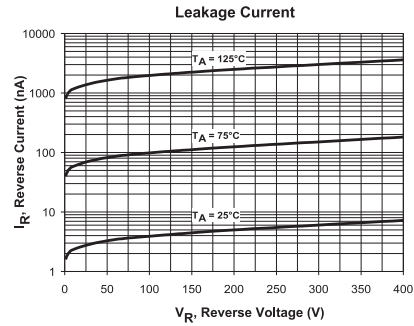
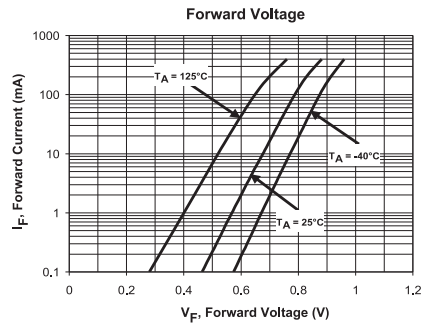
18,080

PRINCIPAL DEVICE TYPES

1N645 thru 1N649
CBRHD-02 Series

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R2 (16- September 2003)



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